Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-19. (Canceled)

20. (Currently amended) A sapphire monocrystal plate for epitaxially growing a semiconductor layer thereon, comprising:

a sapphire monocrystal having a major face, a working reference plane on a peripheral edge of the plate, the working reference plane being substantially parallel or perpendicular to a plane R of the sapphire monocrystal, wherein the major face is a plane A ~~or a plane C~~ of the sapphire monocrystal and has a surface roughness (Ra) of 0.1 μm or less; and

a microcrack line on the major face parallel to the plane R for starting to cleave the plate.

21. (Previously presented) The sapphire monocrystal plate of claim 20, wherein an angle between the working reference plane and the plane R is between –10 to +10 degrees or about 80 to 100 degrees.

22. (Canceled)

23. (Currently amended) A sapphire monocrystal plate for epitaxially growing a semiconductor layer thereon, comprising:

a sapphire monocrystal having a major face, a working reference plane on a peripheral edge of the plate, the working reference plane being substantially parallel or perpendicular to a plane R of the sapphire monocrystal, wherein the major face is a plane A ~~or a plane C~~ of the sapphire monocrystal and has a surface roughness (Ra) of 0.1 μm or less, wherein a semiconductor layer produced by epitaxial growth is on the major face; and

a microcrack line on the major face parallel to the plane R for starting to cleave the plate.

24. (Previously presented) The sapphire monocrystal plate of claim 23, wherein an angle between the working reference plane and the plane R is between –10 to +10 degrees or about 80 to 100 degrees.

25. (Canceled)